

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

3/A
2/26/11
D. Scott

In re Application of:

Yoshitaka TSUNASHIMA et al.

Serial Number: Not Yet Assigned

Filed: October 13, 2000

For: SEMICONDUCTOR DEVICE
AND METHOD OF
MANUFACTURING THE SAME

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)
) Prior Application: Rule 53(b) Divisional of
) Serial No.:09/105,958 filed
) June 29, 1998 6184083

) Prior Group Art Unit: 2814

) Prior Examiner: RAO, S.

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application
as follows:

IN THE CLAIMS:

Please cancel claim 2, amend 12, 27 and 28, add claims 30-32, as follows :

- a) 12. (Amended) A semiconductor device comprising :
- a substrate;
- first and second gate insulator films formed on the substrate, the first and
second gate insulator films having different thickness and/or being made of different
materials; and